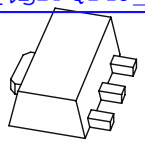

BFQ149

PNP 5 GHz wideband transistor

Rev. 03 — 28 September 2007 Product data sheet

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NXP Semiconductors

PNP 5 GHz wideband transistor BFQ149

DESCRIPTION

PNP transistor in a SOT89 envelope. It is intended for use in UHF applications such as broadband aerial amplifiers (30 to 860 MHz) and in microwave amplifiers such as radar systems, spectrum analysers, etc., using SMD technology.

PINNING

PIN	DESCRIPTION
Code: FG	
1	emitter
2	collector
3	base

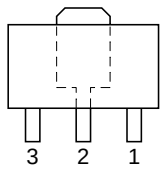


Fig.1 SOT89.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	open base	–	–	–15	V
I_C	DC collector current		–	–	–100	mA
P_{tot}	total power dissipation	up to T_s = 135 °C (note 1)	–	–	1	W
h_{FE}	DC current gain	I_C = –70 mA; V_{CE} = –10 V; T_j = 25 °C	20	50	–	
f_T	transition frequency	I_C = –75 mA; V_{CE} = –10 V; f = 500 MHz; T_j = 25 °C	4	5	–	GHz
G_{UM}	maximum unilateral power gain	I_C = –50 mA; V_{CE} = –10 V; f = 500 MHz; T_{amb} = 25 °C	–	12	–	dB
F	noise figure	I_C = –50 mA; V_{CE} = –10 V; R_s = 60 Ω; f = 500 MHz; T_{amb} = 25 °C	–	3.75	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–20	V
V_{CEO}	collector-emitter voltage	open base	–	–15	V
V_{EBO}	emitter-base voltage	open collector	–	–3	V
I_C	DC collector current		–	–100	mA
I_{CM}	peak collector current	f > 1 MHz	–	–150	mA
P_{tot}	total power dissipation	up to T_s = 135 °C (note 1)	–	1	W
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

PNP 5 GHz wideband transistor BFQ149

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	up to T_s = 135 °C (note 1)	40 K/W

Note

1. T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

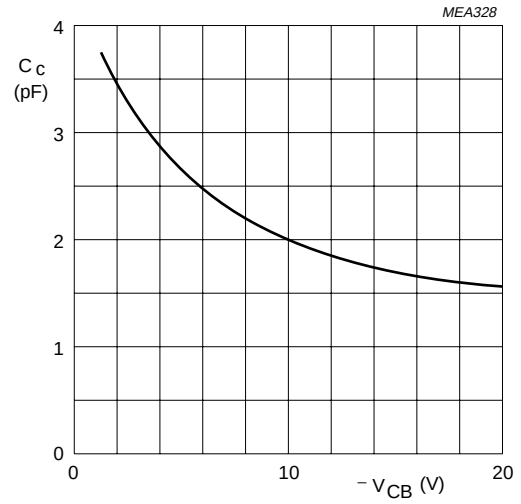
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –10 V;	–	–	100	nA
h_{FE}	DC current gain	I_C = –70 mA; V_{CE} = –10 V	20	50	–	
f_T	transition frequency	I_C = –70 mA; V_{CE} = –10 V; f = 500 MHz; T_{amb} = 25 °C	4	5	–	GHz
C_c	collector capacitance	I_E = 0; V_{CB} = –10 V; f = 1 MHz	–	2	–	pF
C_e	emitter capacitance	I_C = 0; V_{EB} = –0.5 V; f = 1 MHz	–	4	–	pF
C_{re}	feedback capacitance	I_C = 0; V_{CE} = –10 V; f = 1 MHz	–	1.7	–	pF
G_{UM}	maximum unilateral power gain (note 1)	I_C = –50 mA; V_{CE} = –10 V; f = 500 MHz; T_{amb} = 25 °C	–	12	–	dB
F	noise figure	I_C = –50 mA; V_{CE} = –10 V; R_s = 60 Ω; f = 500 MHz; T_{amb} = 25 °C	–	3.75	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

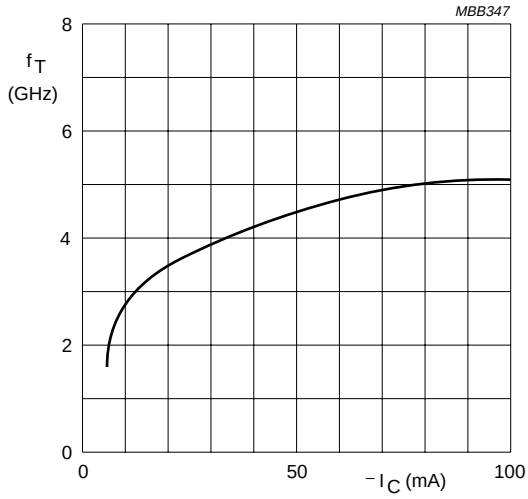
$$G_{UM} = 10 \log \frac{|S_{21}|^2}{\left(1 - |S_{11}|^2\right)\left(1 - |S_{22}|^2\right)} \text{dB}.$$

PNP 5 GHz wideband transistor BFQ149



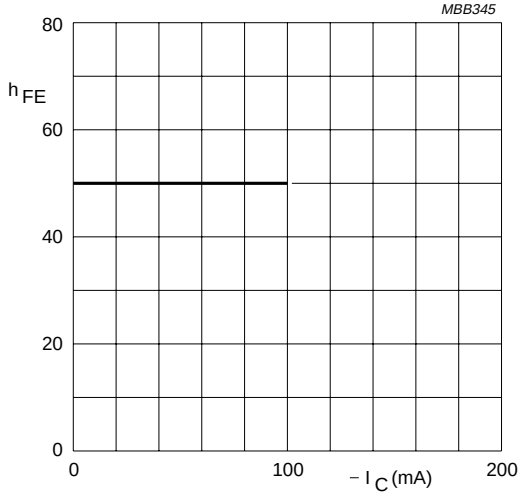
I_E = 0; f = 1 MHz; T_j = 25 °C.

Fig.2 Collector capacitance as a function of collector-base voltage.



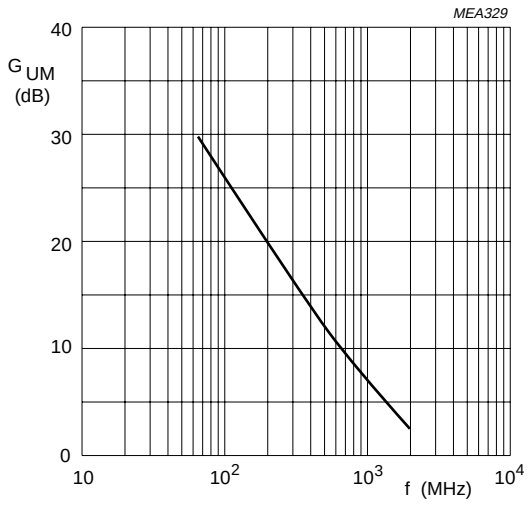
V_{CE} = –10 V; f = 500 MHz; T_{amb} = 25 °C.

Fig.3 Transition frequency as a function of collector current.



V_{CE} = –10 V; T_j = 25 °C.

Fig.4 DC current gain as a function of collector current.

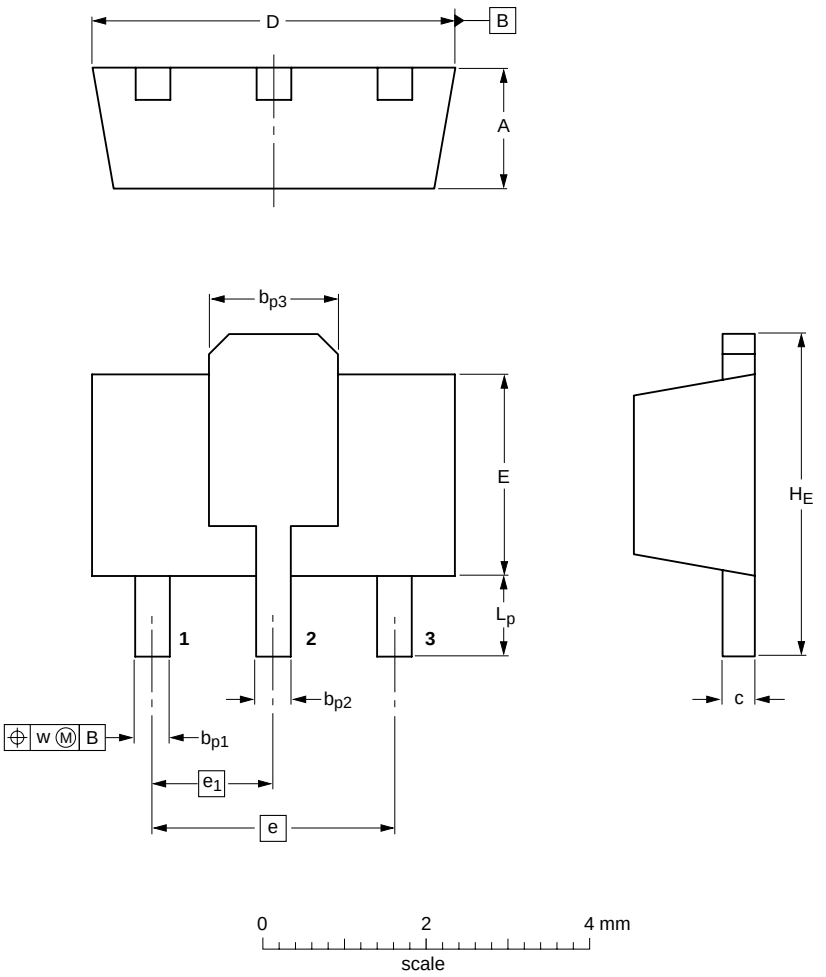


I_c = –50 mA; V_{CE} = –10 V; T_{amb} = 25 °C.

Fig.5 Maximum unilateral power gain as a function of frequency.

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads **SOT89**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT89		TO-243	SC-62			~~06-03-16~~ 06-08-29

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Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFQ149_N_3	20070928	Product data sheet	-	BFQ149_CNV_2
Modifications:	• Fig. 1 and package outline updated			
BFQ149_CNV_2	19950901	Product specification	-	-

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Document identifier: BFQ149_N_3